AMENDMENT TO THE CLAIMS

1. (Currently Amended) A method for fabricating a semiconductor device, said method comprising the steps of:

(a) forming bonding pads above a wafer on which semiconductor elements and an interconnect layer are formed;

(b) forming a passivation film having apertures including regions of the passivation film located above parts of the bonding pads after the step (a);

(c) forming a buffer coat film for covering part of the passivation film after the step (b);

(d) forming, in the buffer coat film, apertures including regions of the buffer coat film extending from an edge of the wafer and located on the whole periphery region having a certain distance from the periphery of the wafer, above scribe line regions and above the parts of the bonding pads, respectively;

(e) bonding a surface protection tape to the wafer using an adhesive material after the step (d); and

(f) polishing the rear surface of the wafer after the step (e).

2. (Original) The method for fabricating a semiconductor device of Claim 1, wherein

in the step (c), the buffer coat film is formed using a positive-type photosensitive material, and

the step (d) includes a process for exposing part of the buffer coat film located on the periphery region of the wafer.

3. (Original) The method for fabricating a semiconductor device of Claim 1, wherein

in the step (c), the buffer coat film is formed using a positive-type photosensitive material, and

the step (d) includes a process for exposing part of the buffer coat film located on the wholes of chip regions at least partly overlapped with the periphery region of the wafer.

4. (Original) The method for fabricating a semiconductor device of Claim 1, wherein

in the step (c), the buffer coat film is formed using an organic resin, and

the step (d) includes a process for selectively removing part of the buffer coat film located on the periphery region of the wafer by a solvent.

5. (Original) The method for fabricating a semiconductor device of Claim 1, wherein

in the step (c), the buffer coat film is formed using an organic resin, and

the step (d) includes a process for blowing gas on part of the buffer coat film located on the periphery region of the wafer before the curing of the buffer coat film.

6. (Currently Amended) A method for fabricating a semiconductor device, said method comprising the steps of:

(a) forming bonding pads above a wafer on which semiconductor elements and an interconnect layer are formed;

(b) forming a passivation film having apertures including regions of the passivation film located above parts of the bonding pads after the step (a);

(c) forming a buffer coat film for covering part of the passivation film after the step (b);

(d) forming, in the buffer coat film, apertures including regions of the buffer coat film located above scribe line regions and above the parts of the bonding pads, respectively, and reducing the thickness of an outermost peripheral part of the buffer coat film located on the whole periphery region of the wafer having a certain distance from the periphery of the wafer;

(e) bonding a surface protection tape to the wafer using an adhesive material after the step (d); and

(f) polishing the rear surface of the wafer after the step (e).

7. (Original) The method for fabricating a semiconductor device of Claim 6, wherein

in the step (d), the thickness of part of the buffer coat film located on the periphery region is reduced to 3μm or less.

8-12. (Canceled)

13. (Previously presented) The method for fabricating a semiconductor device of Claim 1, wherein in the step (d), the whole periphery region refers to circular regions in the periphery of the wafer.

14. (Previously presented) The method for fabricating a semiconductor device of Claim 6, wherein in the step (d), the whole periphery region refers to circular regions in the periphery of the wafer.